ABSTRACT

A trench is formed in a low K dielectric (100) over a plurality of vias (120) also formed in the low K dielectric layer (100). The vias are separated by a distance of less than X_V and the edge of the trench is greater than X_{TO} from the edge α of the via closest to the edge of the trench. The trench and vias are subsequently filled with copper (150), (160) to form the interconnect line.

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